MBF110

Solid-State Fingerprint Sensor

Overview

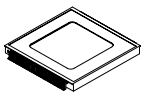
The Fujitsu MBF110 Solid-State Fingerprint Sensor is a direct contact, fingerprint acquisition device. It is a high performance, low power, low cost, capacitive sensor with an integrated two-dimensional array of metal electrodes in the sensing array. Each metal electrode acts as one plate of a capacitor and the contacting finger acts as the second plate. A passivation layer on the device surface forms the dielectric between these two plates. Ridges and valleys on the finger yield varying capacitor values across the array, which is read to form an image of the fingerprint.

The MBF110 is manufactured in standard CMOS technology and is available in an 80-pin, VSPA 80/1 and LQFP 80/1. The 300 × 300 sensor array has a 50 µm pitch and yields a 500-dpi image. The sensor surface is protected by a patented, ultra-hard, abrasion and chemical resistant coating.

Features

- Non-optical solid-state device
- 300 × 300 sensor array, 50 µm pitch
- 1.5 cm × 1.5 cm sensor area
- 500-dpi resolution
- Operation from 3V to 5.5V
- Ultra-hard protective coating
- Integrated 8-bit flash analog-to-digital converter
- 8-bit microprocessor interface
- Standard CMOS technology
- Low power, less than 200 mW

Packages



80-pin SOP (VSPA)

80-pin TSOP (LQFP)

A block diagram of the MBF110 is shown in Figure 1. The MBF110 has an integrated 8-bit flash analog-to-digital converter to digitize the output of the sensor array. The fingerprint image is transmitted on an 8-bit bi-directional bus interface compatible with most microprocessors.

For SETCUR resistor differences between the MBF110 see the Pin Information table.

Applications

- Database and network access
- Portable fingerprint acquisition
- Access control (home, auto, office, etc.)
- ATM
- Smart cards
- Cellular phone security access

Preliminary

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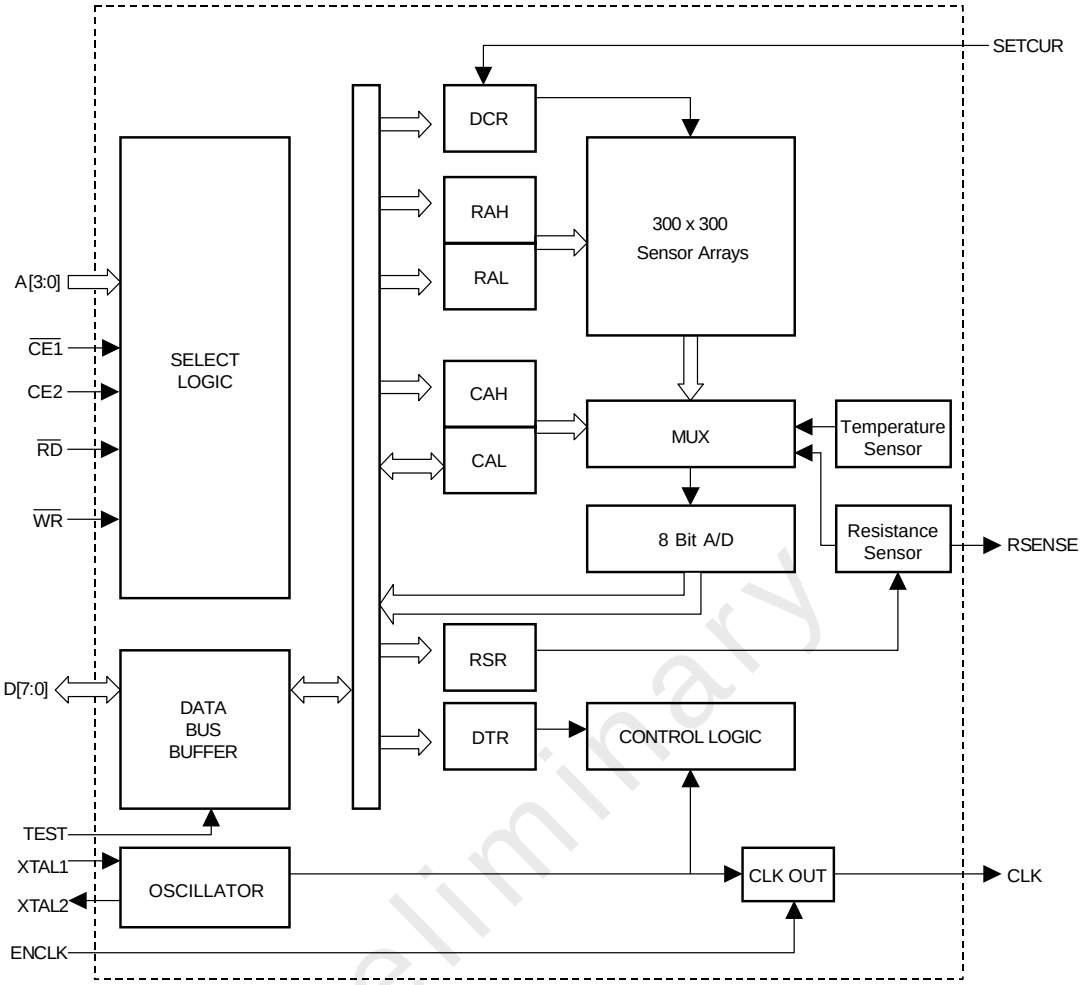

Figure 1. MBF110 Block Diagram

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Chip Operation

The sensor array is composed of 300 rows and 300 columns of sensor plates. Associated with each column are two sample-and-hold circuits. A fingerprint image is sensed or captured one row at a time. This"row capture"occurs in two phases. In the first phase, the sensor plates of the selected row are pre-charged to the V_{DD} voltage. During this pre-charge period, an internal signal enables the first set of sample-and-hold circuits to store the pre-charged plate voltages of the row.

In the second phase, the row of sensor plates is discharged with a current source. The rate at which a cell is discharged is proportional to the"discharge current."After a period of time (referred to as the "discharge time"), an internal signal enables the second set of sample-and-hold circuits to store the final plate voltages. The difference between the pre-charged and discharged plate voltages is a measure of the capacitance of a sensor cell. After the row capture, the cells within the row are ready to be digitized.

The sensitivity of the chip is adjusted by changing the discharge current and discharge time. The nominal value of the current source is controlled by an external resistor connected between the SETCUR pin and ground. The current source is controlled from the Discharge Current Register (DCR). The discharge time is controlled by the Discharge Time Register (DTR).

The sensor array is a row-oriented device. Images are read out one row at a time. The High-Order Row Address Register (RAH) and the Low-Order Row Address Register (RAL) must be programmed to select a row to be captured. Writing to RAL initiates a row capture. The capture time is a function of the external clock and the DTR. After the discharge cycle, the outputs of the row elements will be stored in analog sample and hold circuits.

After the row capture is completed, the High-Order Column Address Register (CAH) and Low-Order Column Address Register (CAL) must be programmed to select an element within the captured row to be digitized. Writing to CAL causes the analog-to-digital (A/D) converter to digitize the difference between the outputs of the two sample-and-holds of the selected column cell. The output of the A/D converter is accessed by reading the CAL register.

Rows can be accessed in any order; however, the selected row must be captured before the column cells are read. The column cells within a row can be accessed in any order.

Special Features

There are two programmable open-drain outputs that can be used for driving LEDs.

The CLKOUT pin can be enabled to output a square-wave clock of the same frequency as the oscillator clock. CLKOUT can be used to drive external circuitry. When ENCLK is high, the clock signal is present at the CLKOUT pin. When ENCLK is low or unconnected, the CLKOUT output is held low.

MBF110 Pin Information for SOP (VSPA) 80/1

Pin Number	Pin Name	Type	Description	Notes
34	A3	Input	Address Inputs	Address signals connected to these pins select a register to read from or write to during data transfer.
35	A2			
36	A1			
37	A0			
38	$\overline{CE1}$		Chip Enable, Active Low	When $\overline{CE1}$ is low and CE2 is high, the chip is selected.
39	CE2		Chip Enable, Active High	When $\overline{CE1}$ is low and CE2 is high, the chip is selected.
40	$\overline{RD}$		Read Enable, Active Low	This pin must be low while $\overline{WR}$ is high and the chip selected in order to read a register on the chip.
17	$\overline{WR}$		Write Enable, Active Low	This pin must be low while the chip is selected to write to a register on the chip.
18	D7	Bi-directional	Data Bus	Inputs when $\overline{WR}$ is low and chip is selected. Outputs when $\overline{RD}$ is low, $\overline{WR}$ is high, and chip is selected.
19	D6			
21	D5			
22	D4			
24	D3			
25	D2			
26	D1			
27	D0			
32	CLKOUT	Output	Clock Output	This pin outputs the oscillator clock frequency when ENCLK is high.
31	ENCLK	Input	Enable Clock Output	A high on this pin enables the CLKOUT pin. A low on this pin holds CLKOUT low. ENCLK has an internal pull-down resistor.
15	LED1	Open-drain Output	LED driver	This pin can be used to drive an LED.
14	LED2	Open-drain Output		
3	SETCUR	Input	Set Discharge Current	Place an external resistor R1 (200K – 680K ohms) between this pin and ground. Typical: FPS110, R1 = 680K; FPS110B, R1 = 200K; FPS110E, R1 = 200K
2	N/A		Reserved pin	Must be left disconnected.
13	TEST			
20, 33	V_{DD}	Power	Digital Power Supply	
1	V_{DDA}		Analog Power Supply	

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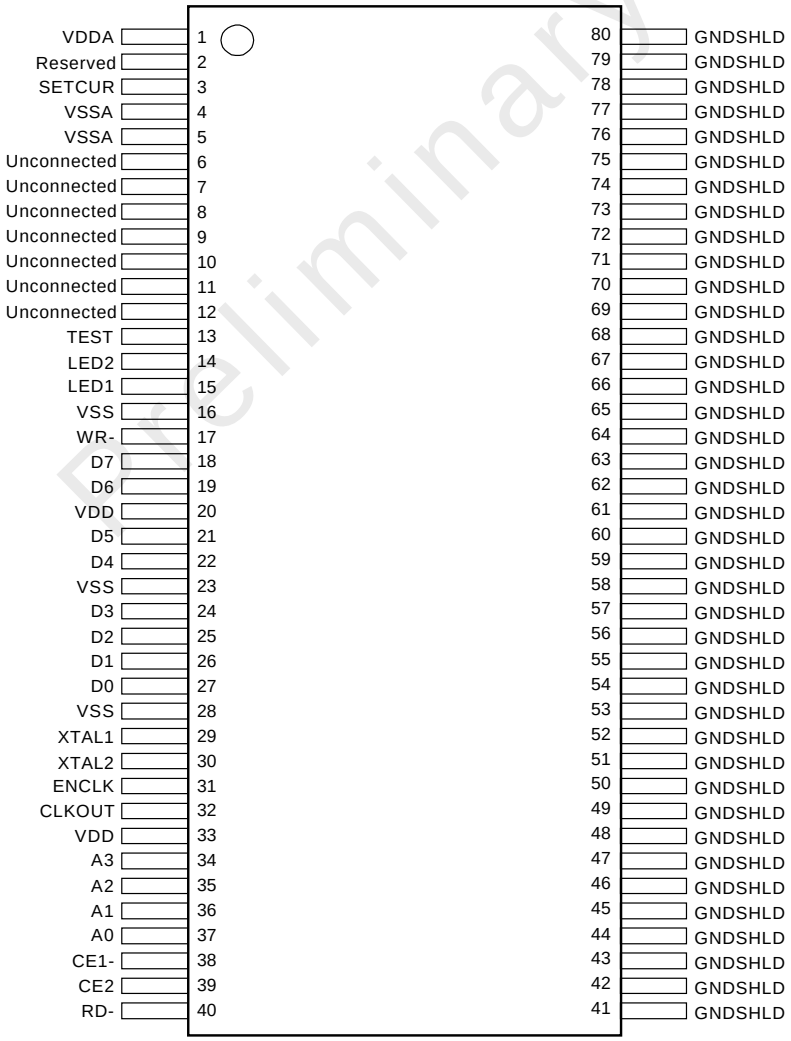
MBF110 Pin Information for SOP (VSPA) 80/1 (Continued)

Pin Number	Pin Name	Type	Description	Notes
16, 23, 28	V_{SS}	Ground	Digital ground	
4, 5	V_{SSA}	(Center)	Analog ground	
29	XTAL1	Input	Input to the On-Chip Oscillator	To use the internal oscillator connect a crystal circuit to this pin. If an external oscillator is used, its output is connected to this pin. XTAL1 is the clock source for internal timing.
30	XTAL2	Output	Output of the On-Chip Oscillator	To use the internal oscillator connect a crystal circuit to this pin. If an external oscillator is used, leave XTAL2 unconnected.
41-80	GNDSHLD	Shield Ground	Connected to Package Top Plate	These pins should connect to chassis ground.
2, 6-12	N/A	N/A		Not connected.

MBF110 Connection Diagram



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Function Table

$\overline{CE1}$	CE2	$\overline{RD}$	$\overline{WR}$	Mode	Data Lines
H	X	X	X	De-selected	High-Z
X	L	X	X	De-selected	High-Z
L	H	H	H	Standby	High-Z
L	H	L	H	Read	Data Out
L	H	H	L	Write	Data In

Register Map

A3	A2	A1	A0	Access	Register	Description
0	0	0	0	Write	RAL	Low Order Row Address Register
0	0	0	1	Write	RAH	High Order Row Address Register
0	0	1	0	Read/Write	CAL	Low Order Column Address Register
0	0	1	1	Write	CAH	High Order Column Address Register
0	1	0	0	Write	DTR	Discharge Time Register
0	1	0	1	Write	DCR	Discharge Current Register
0	1	1	0	Write	RSR	Reserved

Address Register Descriptions

Refer to *Row Capture and A/D Conversion Timing* on page 9 to calculate row capture and A/D conversion times.

RAL (A3-A0 Address 0000) Write Only

Low Order Row Address Register

This register and bit 0 of RAH form the 9-bit Row Address Register that selects the row to be captured. The 9-bit Row Address Register selects a row address from 0 through 299. Writing the RAL starts a row capture. Only RAL has to be written if RAH doesn't change, otherwise RAH has to be written before RAL.

MSB LSB

BIT7	BIT6	BIT5	BIT4	BIT3	BIT2	BIT1	BIT0
RA7	RA6	RA5	RA4	RA3	RA2	RA1	RA0

Bit Number	Bit Name	Function
[7:0]	RA[7:0]	Low eight bits of Row Address Register.

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RAH (A3-A0 Address 0001) Write Only

High Order Row Address Register

Bit 0 of this register and RAL form the 9-bit Row Address Register that selects the row to be converted. The L1 and L2 bits control two open-drain outputs that can be used to drive LEDs.

MSB LSB

BIT7	BIT6	BIT5	BIT4	BIT3	BIT2	BIT1	BIT0
L1	L2	–	–	–	–	–	RA8

Bit Number	Bit Name	Function
7	L1	L1=0, LED1 output low L1=1, LED1 output high-Z
6	L2	L2=0, LED 2 output low L2=1, LED 2 output high-Z
[5:1]	–	Reserved, write 0 to these bits.
0	RA8	MSB of Row Address

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CAL (A3-A0 Address 0010) Read/Write

Low Order Column Address Register

CAL is a read/write register. Writing to this address writes to the low-order 8 bits of the 9-bit Column Address Register. The 9-bit Column Address Register selects a column from 0 through 299. Writing to CAL causes the analog-to-digital (A/D) converter to begin digitizing its input. The input of the A/D converter is selected by bits 7 and 6 of the CAH register. The user should wait until the row capture is completed before writing to the CAL.

Reading from this address returns the output of the A/D converter. After writing to CAL, the user should wait until A/D conversion completes before reading the A/D converter.

MSB LSB

BIT7	BIT6	BIT5	BIT4	BIT3	BIT2	BIT1	BIT0
CA7	CA6	CA5	CA4	CA3	CA2	CA1	CA0

Bit Number	Bit Name	Function
[7:0]	CA[7:0]	(WRITE) Low eight bits of Column Address Register. (READ) Output of A/D converter.

CAH (A3-A0 Address 0011) Write Only

High Order Column Address Register

Bit 0 of this register and CAL form the 9-bit Column Address Register that selects a cell from the current row for digitizing. The user should wait until the row capture is completed before writing to CAH.

MSB LSB

BIT7	BIT6	BIT5	BIT4	BIT3	BIT2	BIT1	BIT0
R	T	–	–	–	–	–	CA8

Bit Number	Bit Name	Function
[7:1]	–	Reserved, write 0 to these bits.
0	CA8	MSB of Column Address Register

DTR (A3-A0 Address 0100) Write Only

Discharge Time Register

MSB LSB

BIT7	BIT6	BIT5	BIT4	BIT3	BIT2	BIT1	BIT0
PD	T6	T5	T4	T3	T2	T1	T0

Bit Number	Bit Name	Function
7	PD	Power down chip. PD=0, Chip in Normal Mode PD=1, Chip in Low Power Mode
[6:0]	T[6:0]	Selects the count to be loaded into the Discharge Timer. Discharge time is selected in increments of the oscillator period. Discharge Time is defined as the period between the sampling and holding of the pre-charged sensor cell to the sampling and holding of the discharging sensor cell. The Discharge Time can be calculated from the following equation: Discharge Time = T[6:0] * t_{OSC}

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DCR (A3-A0 Address 0101) Write Only

Discharge Current Register

MSB LSB

BIT7	BIT6	BIT5	BIT4	BIT3	BIT2	BIT1	BIT0
F2	F1	TRST	DC4	DC3	DC2	DC1	DC0

Bit Number	Bit Name	Function
[7:6]	F2, F1	These two bits tell the chip the frequency of the external oscillator or crystal that is connected to the chip. F2 F1 XTAL Input 0 0 10-15 MHz 0 1 15-20 MHz 1 0 20-30 MHz 1 1 30-40 MHz
5	TRST	Timer Reset. Set this bit to halt and reset the Discharge Timer. Resetting the Discharge Timer is necessary to put the Discharge Timer in a known state after power-up or after returning to Normal mode from Low-power mode (See bit 7 of DTR). TRST=0,Normal Timer Operation TRST=1,Halt and Clear Discharge Timer (doesn't clear DTR)
[4:0]	DC[4:0]	Selects the Discharge Current source value.

RSR (A3-A0 Address 0110) Write Only

Reserved

The user must initialize this resistor to zero.

MSB LSB

BIT7	BIT6	BIT5	BIT4	BIT3	BIT2	BIT1	BIT0
–	–	–	–	–	–	–	–

Bit Number	Bit Name	Function
[7:0]	–	Reserved. Write 0 to these bits.

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Row Capture and A/D Conversion Timing

F2	F1	XTAL Input Range	Row Capture Time in OSC Clock Periods	A/D Conversion Time in OSC Clock Periods
0	0	10-15 MHz	18+n	13
0	1	15-20 MHz	24+n	15
1	0	20-30 MHz	36+n	23
1	1	30-40 MHz	48+n	30

NOTE: n is selected by bits T[6:0] of DTR.

A/D Converter

The integrated 8-bit flash A/D converter is a buffered device. Each write to CAL causes: 1) the result of the previous conversion to be latched and made readable at CAL, and 2) the A/D converter to start digitizing its current input. Consequently, it takes 301 writes to CAL in order to digitize the 300 cells of a row.

Specifications*

*All specifications in this document are preliminary and subject to change.

Absolute Maximum Ratings

- Storage Temperature: -65° to +150° C
- DC Voltage Applied to any Pins: -0.5 V to +7.0 V

Operating Range

Symbol	Parameter	Min	Max	Unit
V_{DD}	Digital Supply Voltage	+3.0	+5.5	V
V_{DDA}	Analog Supply Voltage	+3.0	+5.5	V
	Standard Temperature Range	0	60	°C
f_{OSC}	Oscillator Frequency V_{DD} = 5.0V	10	40	MHz
	V_{DD} = 3.0V	10	20	MHz

DC Electrical Characteristics

Symbol	Parameter	Test Conditions	Min	Max	Unit
V_{OH}	Output High Voltage	V_{DD} = 4.5V, I_{OH} = -4 mA	2.4	–	V
V_{OL}	Output Low Voltage	V_{DD} = 4.5V, I_{OL} = 8 mA	–	0.4	V
V_{OH}	Output High Voltage	V_{DD} = 3.0V, I_{OH} = -2 mA	2.4	-	V
V_{OL}	Output Low Voltage	V_{DD} = 3.0V, I_{OL} = 4 mA	–	0.4	V
V_{IH}	Input High Voltage		2.0	V_{DD}	V
V_{IL}	Input Low Voltage	V_{DD} = 4.5V	-0.5	0.8	V
V_{IL}	Input Low Voltage	V_{DD} = 3.00	-0.5	0.6	V
I_{LI}	Input Leakage Current	GND ≤ V_{in} ≤ 5.5V	-5.0	5.0	µA
I_{LO}	Output Leakage Current	GND ≤ V_{out} ≤ 5.5V	-5.0	5.0	µA

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Power Supply Characteristics (V_{DD} = 5.5V, f_{OSC}=40 MHz Standard Temperature Range)

Symbol	Parameter	Test Conditions	Typ		Max		Unit
			LP	STD	LP	STD	
I_{DD1}	Digital Supply Current	Power down with CLKOUT disabled, (DTR bit 7 = 1, ENCLK = 0)	<1	100	50	100	µA
I_{DD2}		Power down with CLKOUT enabled. (DTR bit 7 = 1, ENCLK = 1)	17	20	20	25	mA
I_{DD3}		Idle with CLKOUT disabled. (DTR bit 7 = 0, ENCLK = 0)	8	10	12	15	mA
I_{DD4}		Idle with CLKOUT enabled. (DTR bit 7 = 0, ENCLK = 1)	17	20	20	25	mA
I_{DD5}		Active A/D conversion with CLKOUT disabled. (DTR bit 7 = 0, ENCLK = 0)	15	20	25	30	mA
I_{DD6}		Active A/D conversion with CLKOUT enabled. (DTR bit 7 = 0, ENCLK = 1)	25	30	30	35	mA
I_{DDA}	Analog Supply Current	Power down with CLK disabled or enabled. (DTR bit 7 = 1)	<10	<100	50	1000	µA
		IDLE with CLKOUT disabled or enabled, (DTR bit 7 = 0)	15	20	22	25	mA
		Active A/D conversion with CLKOUT disabled or enabled. (DTR bit 7 = 0)	18	22	26	30	mA

Note: Analog supply currents are independent of f_{OSC}
Note: XTAL2 & CLKOUT driving C_{LOAD} = 50pF

Power Supply Characteristics V_{DD} = 3.6V, Commercial Temperature Range, f_{OSC} = 20 MHz

Symbol	Parameter	Test Conditions	Typ		Max		Unit
			LP	STD	LP	STD	
I_{DD1}	Digital Supply Current	Power down with CLKOUT disabled. (V_{DD} = max, f_{OSC} = max, DTR bit 7 = 1, ENCLK = 0)	<1	<10	50	100	µA
I_{DD2}		Power down with CLKOUT enabled. (V_{DD} = max, f_{OSC} = max, DTR bit 7 = 1, ENCLK = 1)	6	10	10	15	mA
I_{DD3}		Idle with CLKOUT disabled. (V_{DD} = max, f_{OSC} = max, DTR bit 7 = 0, ENCLK = 0)	3	5	6	10	mA
I_{DD4}		Idle with CLKOUT enabled. (V_{DD} = max, f_{OSC} = max, DTR bit 7 = 0, ENCLK = 1)	6	10	10	15	mA
I_{DD5}		Active A/D conversion with CLKOUT disabled. (V_{DD} = max, f_{OSC} = max, DTR bit 7 = 0, ENCLK = 0)	6	10	10	15	mA
I_{DD6}		Active A/D conversion with CLKOUT enabled. (V_{DD} = max, f_{OSC} = max, DTR bit 7 = 0, ENCLK = 1)	9	13	13	18	mA
I_{DDA}	Analog Supply Current	Power down with CLK disabled or enabled. (V_{DDA} = max, DTR bit 7 = 1)	<2	<10	50	1000	µA
		IDLE with CLKOUT disabled or enabled, (DTR bit 7 = 0)	10	15	15	20	mA
		Active A/D conversion with CLKOUT disable or enable. (DTR bit 7 = 0)	12	15	18	25	mA

Note: Analog supply currents are independent of f_{OSC}
Note: XTAL2 & CLKOUT driving C_{LOAD} = 50 Pf

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Read Cycle Timing at V_{DD} = 3.0V, Standard Temperature Range

Parameter	Description	Min	Max	Unit
t_{AAC}	Address valid to data valid.	–	70	ns
t_{RC}	Read Cycle Time	70	–	ns
t_{ACE1}	$\overline{CE1}$ low to data valid	–	70	ns
t_{ACE2}	CE2 high to data valid	–	70	ns
t_{DOE}	$\overline{RD}$ low to data valid	–	35	ns
t_{LZOE}	$\overline{RD}$ low to low Z	5	–	ns
t_{HZOE}	$\overline{RD}$ high to high Z	–	30	ns
t_{LZCE}	$\overline{CE1}$ low and CE2 high to low Z	5	–	ns
t_{HZCE}	$\overline{CE1}$ high to high Z or CE2 low to high Z	–	30	ns
t_{LZWE}	$\overline{WR}$ high to low Z	5	–	ns
t_{HZWE}	$\overline{WR}$ low to high Z	–	30	ns

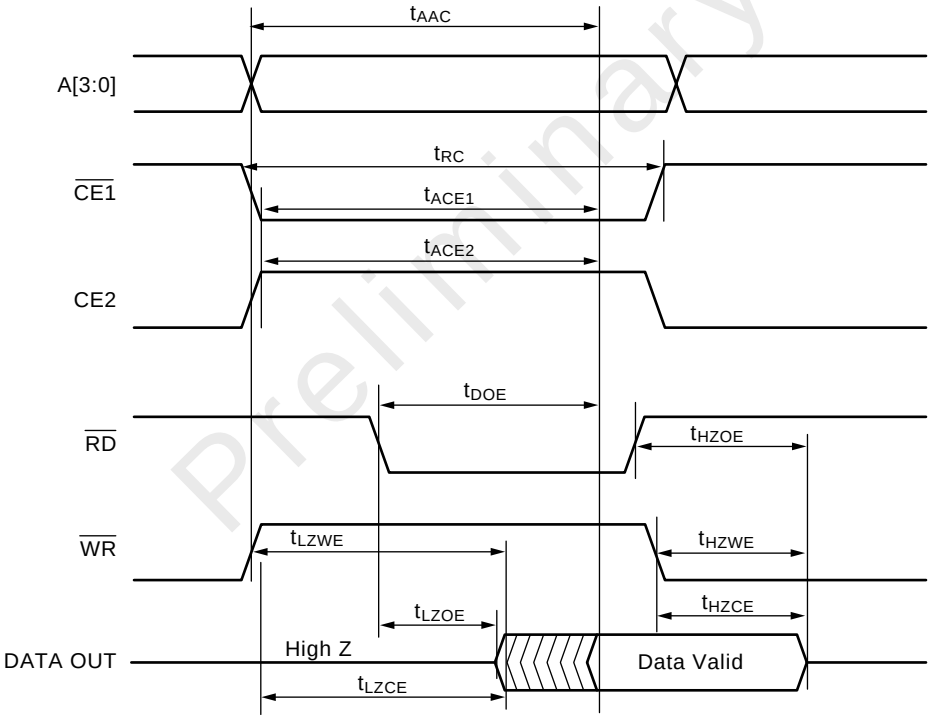

Figure 2. Read Cycle Timing

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Write Cycle Timing at V_{DD} = 3.0V, Standard Temperature Range

Parameter	Description	Min	Max	Unit
t_{WC}	Write Cycle	70	–	ns
t_{SCE1}	$\overline{CE1}$ low to write end	60	–	ns
t_{SCE2}	CE2 high to write end	60	–	ns
t_{AW}	Address setup to write end	55	–	ns
t_{HA}	Address hold from write end	5	–	ns
t_{SA}	Address set-up to write start	5	–	ns
t_{PWE}	$\overline{WR}$ Pulse Width	40	–	ns
t_{SD}	Data setup to write end	35	–	ns
t_{HD}	Data hold from write end	5	–	ns

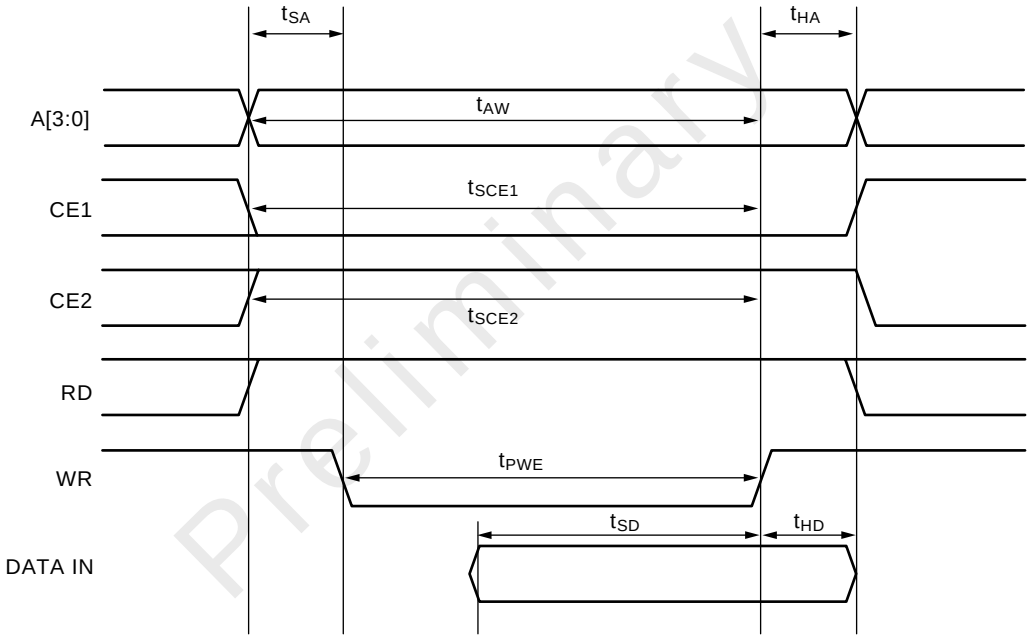

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Figure 3. Write Cycle Timing

Power Up and Initialization

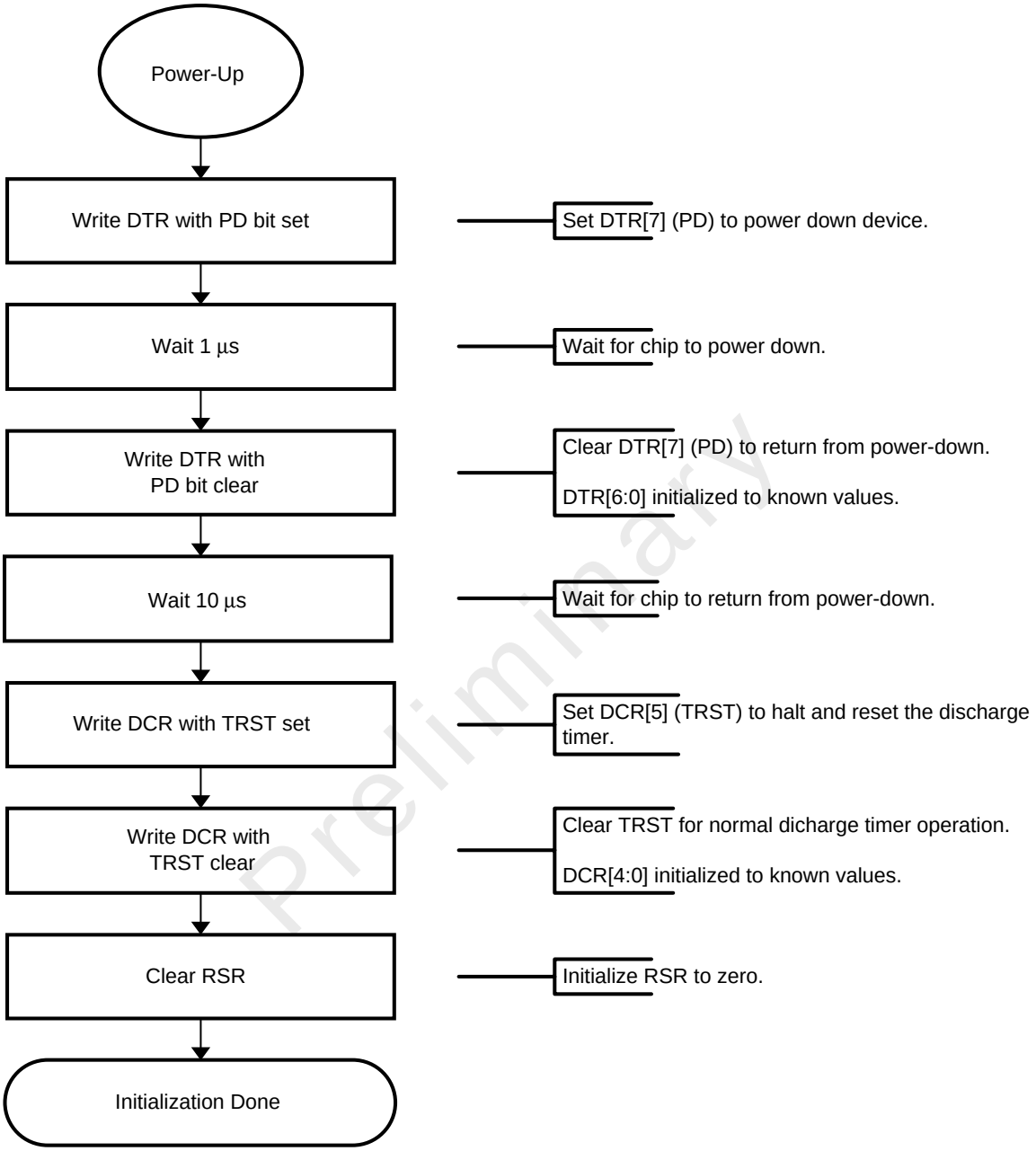

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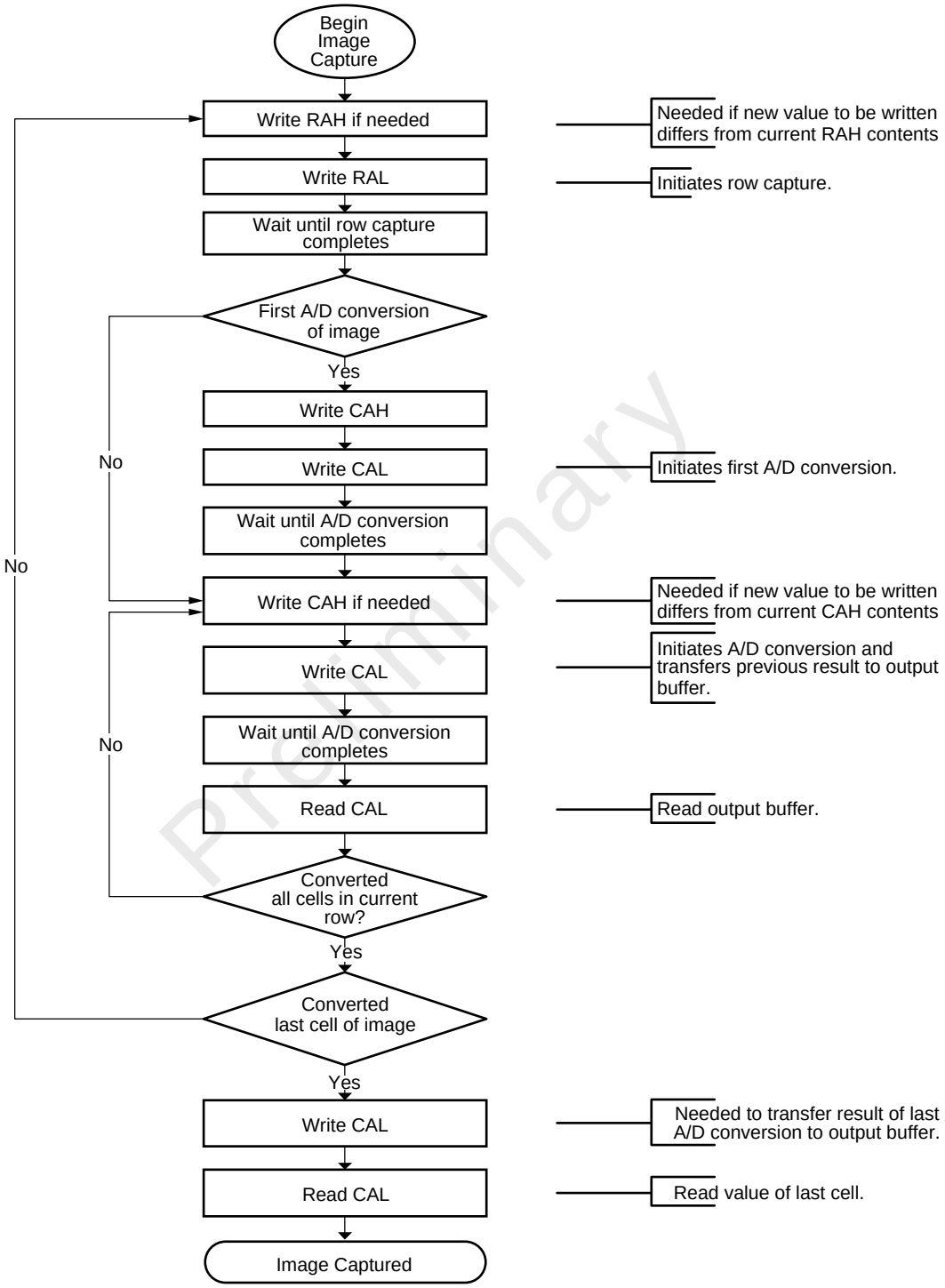
Image Capture



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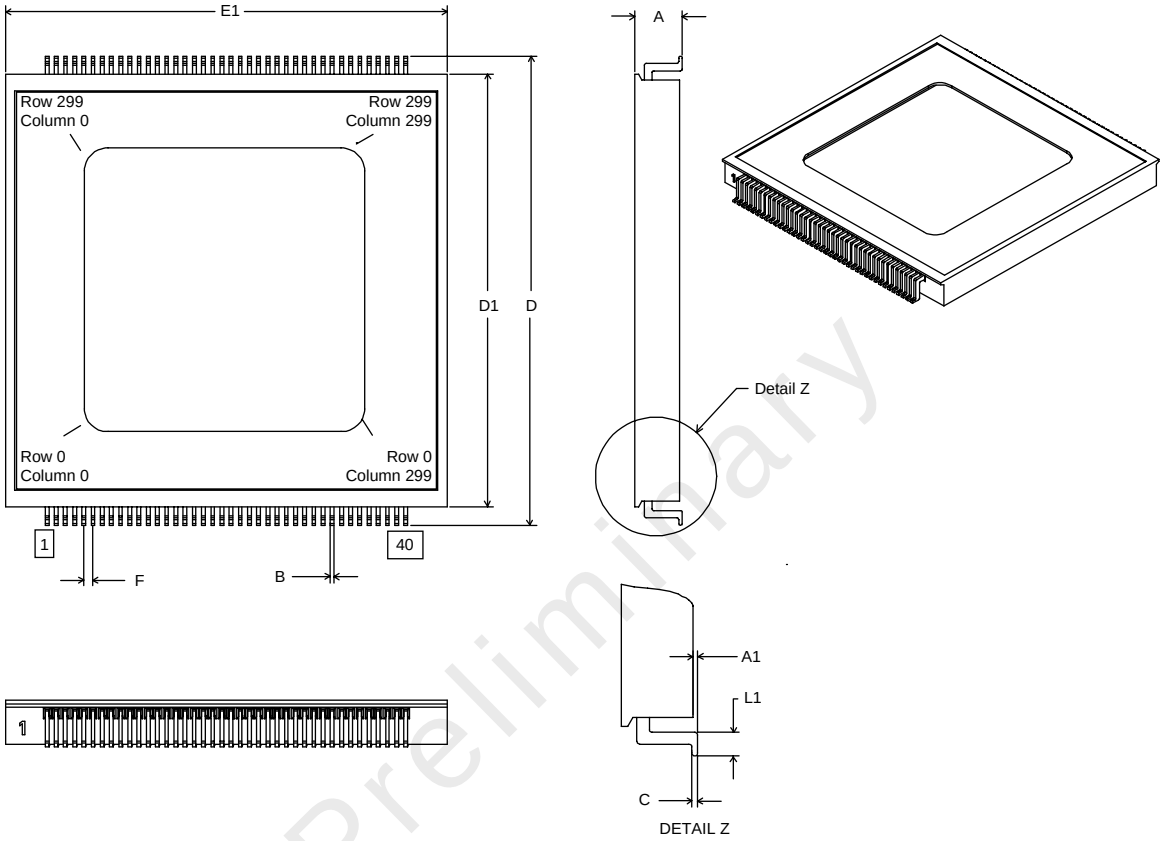
MBF110 – PFW1

SOP (VSPA) – 80 pin Package

MBF110-PFW1: SOP 80pin Assembly Diagram



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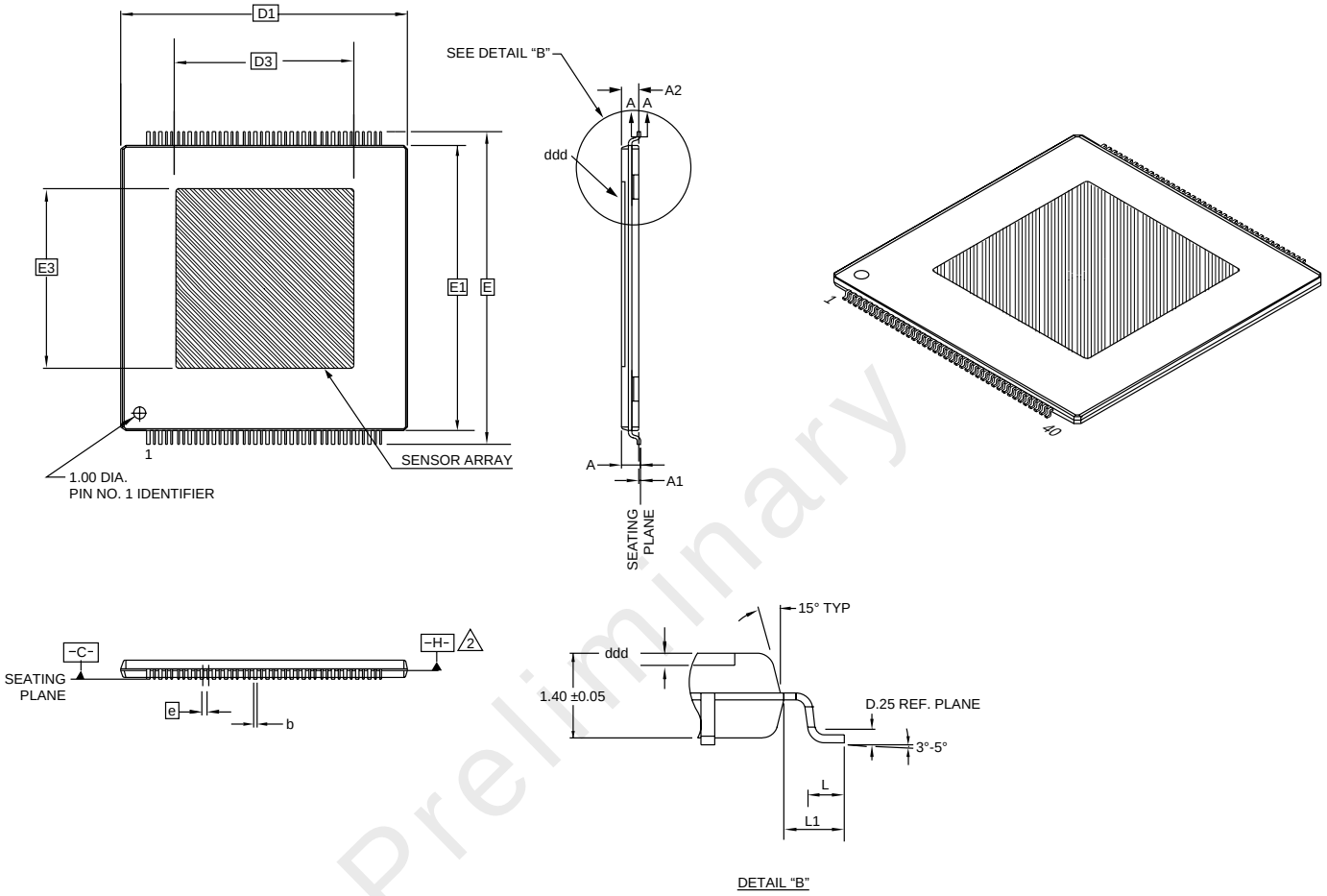
MBF110 Dimensions				
Symbol	**Description**	**Min**	**Nom**	**Max**
N	Pin Count		80	
A	Overall Height		.102 (2.60)	
A1	Stand Off		.006 (.15)	
B	Pin Width		.008 (.20)	
C	Pin Thickness		.008 (.20)	
D	Tip to tip Dimension	1.016 (25.8)	1.025 (26.0)	1.032 (26.2)
D1	Package Body	.941 (23.9)	.945 (24.0)	.949 (24.1)
E1	Package Body	.941 (23.9)	.945 (24.0)	.949 (24.1)
F	Pin Pitch	.0187 (.47)	.0197 (.50)	.0207 (.53)
L1	Foot length		.032 (.81)	
Note: Dimensions are in inches (mm)				

MBF110 – PFW

TSOP (LQFP)– 80 pin Package

MBF110-PFW: TSOP 80pin Assembly Diagram



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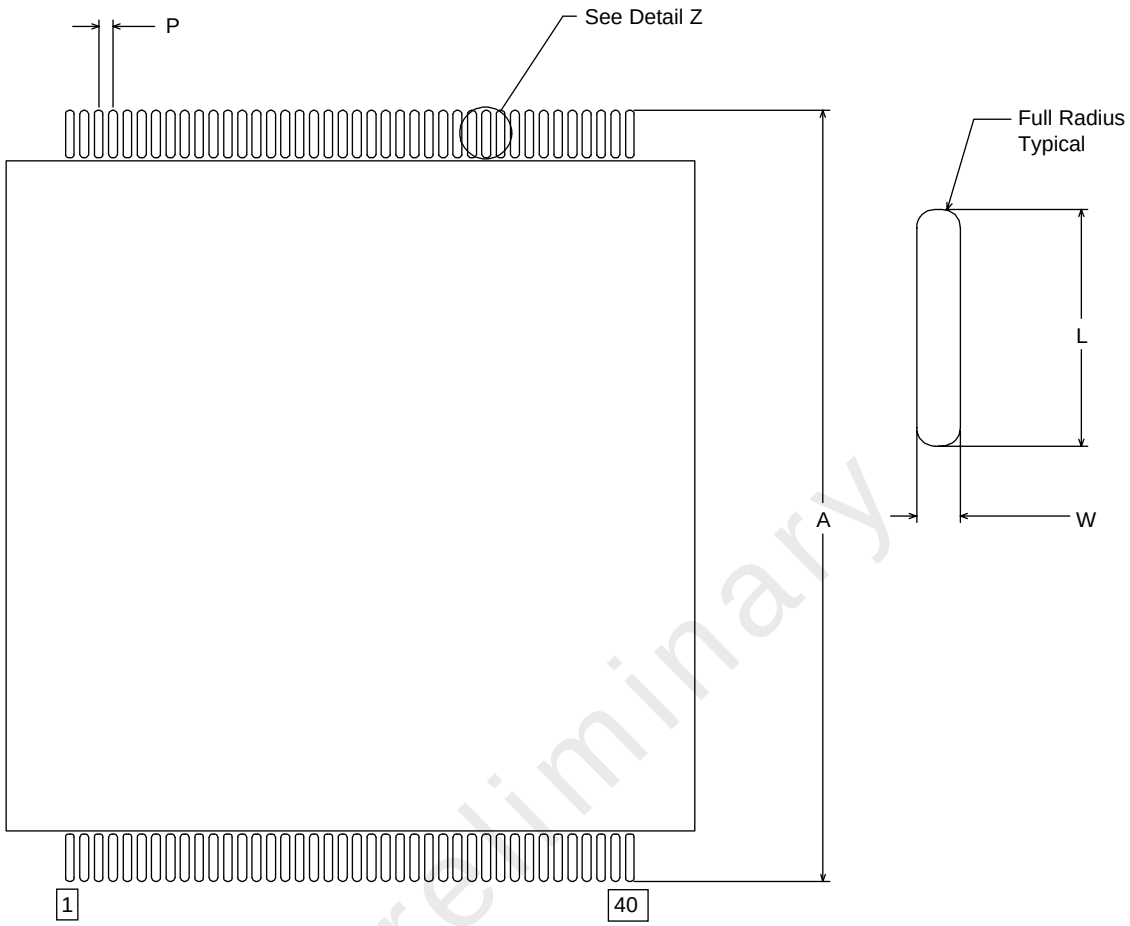
Symbol	MBF110PFW Description	DIMENSIONS					
		Millimeters			Inches		
		Min.	Nom.	Max.	Min.	Nom.	Max.
A	Overall Height	1.45	1.55	1.70	0.57	0.61	0.67
A1	Stand Off	0.10	0.15	0.25	.004	.006	.010
A2	Package Thickness	1.35	1.40	1.45	.053	.055	.057
b	Lead Width	0.16	0.25	0.30	.006	.010	.012
D1	Package Body		24.00 BSC.			.945 BSC.	
D3	Sensor Array Width	14.95	15.00	15.05	.588	.590	.592
ddd	Sensor Array Depth	0.25	0.30	0.35	.010	.012	.014
E	Tip to Tip Dimension		26.00 BSC.			1.024 BSC.	
E1	Package Body		24.00 BSC.			.945 BSC.	
E3	Sensor Array Height	14.95	15.00	15.05	.588	.590	.592
e	Lead Pitch		0.50 TYP.			.0197 TYP.	
L	Lead Length	0.50	0.60	0.70	.020	.024	.028
L1	Foot Length		1.00 REF.			.039 REF.	

MBF110 Solder Pad Layout



Preliminary

Symbol	Description	Dimension
N	Pin Count	80
A	Tip to Tip Dimension	1.074 (27.30)
P	Pitch	.0197 (.50)
L	Pad Length	.065 (1.65)
W	Pad Width	.012 (.30)
Note: Dimensions are in inches (mm)		

Manufacturing Considerations

CAUTION: DO NOT USE ANY METAL PICKUP TOOLS WHICH WOULD CONTACT THE SENSOR DEVICE SURFACE WITHOUT PROTECTIVE LID INSTALLED

- Surface Mount reflow temperature:

  Recommended 220°C Max reflow spike*
  Max Temp 240°C

- Avoid any high pressure spray directly to the sensor device surface.
- Use standard handling practices for ESD sensitive devices.
- Refer to Fujitsu PCB Assembly for Biometric Sensor Guidelines.

Array Pixel Specifications:

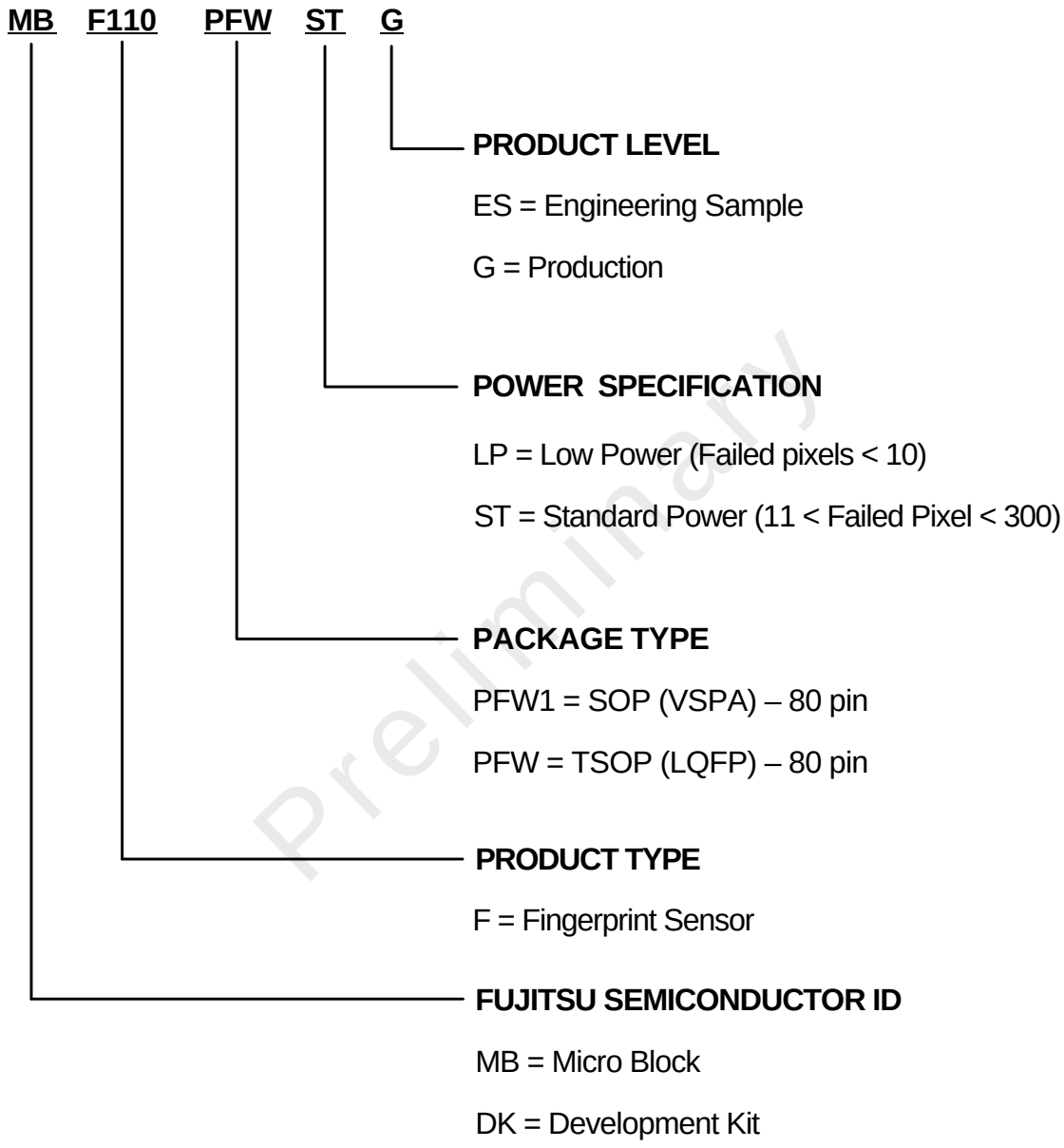
Specification	MBF110-LP	MBF110-STD
Max Failed Pixels	10	300
Max Failed Rows	0	1 (see note 1)
Max Failed Columns	0	1 (see note 1)

Notes: 1) Failing rows or columns that fall on rows (0-4) or (295-299) or columns (0-4) or (295-299) are allowed to pass for the STD product due to packaging overlap at the edge of the sensor array. Failed rows or columns at the extreme edge of the array do not affect the quality of the acquired fingerprint image.

Preliminary

MBF110 Ordering Information

MBF110 Part Number Description:



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FUJITSU MICROELECTRONICS EUROPE GmbH

Am Siebenstein 6-10, 63303 Dreieich-Buchschlag Germany

Tel: (49) 6103-690-0 Fax: (49) 6103-690-122
Web Site: http://www.fme.fujitsu.com